## **SAMYANG ELECTRONICS**

### SCHOTTKY BARRIER RECTIFIER

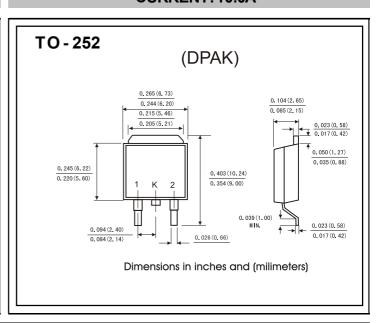
VOLTAGE RANGE: 20 --- 200 V CURRENT: 10.0A

### **FEATURES**

- Metal-semiconductor junction with guard ring
- Epitaxial construction

- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications

### **MECHANICAL DATA**



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

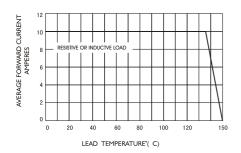
|  | Symbols         | SR<br>1020 | SR<br>1030 | SR<br>1040 | SR<br>1050 | SR<br>1060 | SR<br>1080 | SR<br><b>10100</b> | SR<br>10150 | SR<br>10200 | Units |
|--|-----------------|------------|------------|------------|------------|------------|------------|--------------------|-------------|-------------|-------|
| Maximum repetitive peak reverse voltage  | Vrrm            | 20         | 30         | 40         | 50         | 60         | 80         | 100                | 150         | 200         | Volts |
| Maximum RMS voltage  | Vrms            | 14         | 21         | 28         | 35         | 42         | 56         | 70                 | 105         | 140         | Volts |
| Maximum DC blocking voltage  | VDC             | 20         | 30         | 40         | 50         | 60         | 80         | 100                | 150         | 200         | Volts |
| Maximum average forward rectified current (see Fig.1)  | I(AV)           | 10.0       |            |            |            |            |            |                    |             | Amps        |       |
| Peak forward surge current 8.3ms single half<br>sine-wave superimposed on rated load<br>(JEDEC method) | İFSM            | 150.0      |            |            |            |            |            |                    |             |             | Amps  |
| Maximum instantaneous forward voltage at 10.0 A(Note 1)  | VF              | 0. 60      |            |            | (          | 0.75       | 0.85       |                    | 0.90        | 0.95        | Volts |
| Maximum instantaneous reverse current at rated DC blocking   | <b>I</b> R      | 0.2        |            |            |            |            |            |                    |             | mA          |       |
| voltage(Note 1) $T_A = 125^{\circ}C$   |                 | 15 50      |            |            |            |            |            |                    |             |             |       |
| Typical thermal resistance (Note 2)  | $R_{\theta}$ JC | 2.5        |            |            |            |            |            |                    |             | *C/W        |       |
| Operating junction temperature range   | TJ              | -65 to+150 |            |            |            |            |            |                    |             |             | °C    |
| Storage temperature range  | Tstg            | -65 to+150 |            |            |            |            |            |                    |             | .c          |       |

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

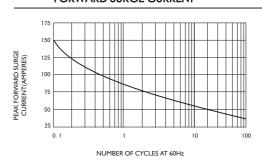
- 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 3. Thermal resistance junction to ambient

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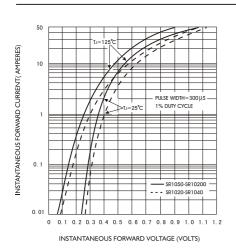
#### FIG.1-FORWARD CURRENT DERATING CURVE



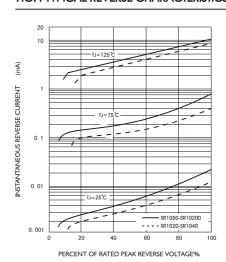
# FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



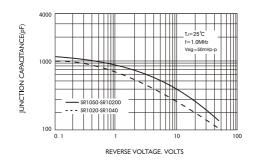
# FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



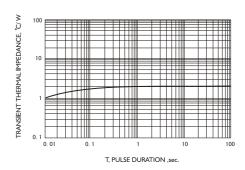
#### FIG.4-TYPICAL REVERSE CHARACTERISTICS



### FIG.5-TYPICAL JUNCTION CAPACITANCE



### FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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